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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/710,596	07/23/2004	Mou-Shiung Lin	MEGP0027USA4	4595

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NORTH AMERICA INTELLECTUAL PROPERTY CORPORATION		
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EXAMINER	
MATTHEWS, COLLEEN ANN	

ART UNIT	PAPER NUMBER
2811	

NOTIFICATION DATE	DELIVERY MODE
06/27/2008	ELECTRONIC

Please find below and/or attached an Office communication concerning this application or proceeding.

The time period for reply, if any, is set in the attached communication.

Notice of the Office communication was sent electronically on above-indicated "Notification Date" to the following e-mail address(es):

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Office Action Summary	Application No.		Applicant(s)	
	10/710,596		LIN, MOU-SHIUNG	
	Examiner		Art Unit	
	Colleen A. Matthews		2811	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) OR THIRTY (30) DAYS, WHICHEVER IS LONGER, FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If NO period for reply is specified above, the maximum statutory period **will** apply and **will** expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply **will**, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☒ Responsive to communication(s) filed on 31 March 2008.
- 2a) ☒ This action is **FINAL**. 2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 43-74, 83, 84 and 89-102 is/are pending in the application.
- 4a) Of the above claim(s) _____ is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 43-74, 83, 84 and 89-102 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
 2. ☐ Certified copies of the priority documents have been received in Application No. _____.
 3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- | | |
|--|---|
| 1) <input checked="" type="checkbox"/> Notice of References Cited (PTO-892) | 4) <input type="checkbox"/> Interview Summary (PTO-413) |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | Paper No(s)/Mail Date. _____ |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO/SB/08) | 5) <input type="checkbox"/> Notice of Informal Patent Application |
| Paper No(s)/Mail Date _____ | 6) <input type="checkbox"/> Other: _____ |

DETAILED ACTION

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 43, 48-53, 89 and 94-99 are rejected under 35 U.S.C. 103(a) as being unpatentable over U.S. Pat. No. 6,495,442 to Lin et al (Lin) in view of U.S. Pat. No. 6,528,380 to Woolery et al. (Woolery).

Re claim 43: Lin discloses a chip structure comprising:

a silicon substrate (10, col 4 line 49);

a resistor in said silicon substrate (not shown but “transistors and other devices” is described in col 4 lines 49-51),

a MOS device (not shown but described as “transistors and other devices” in col 4 lines 49-51) comprising a portion in said silicon substrate;

a metallization structure (14) over said silicon substrate, wherein said metallization structure comprises a first metal layer (interconnect portion 13 of first layer of 14) and a second metal layer (interconnect portion 13 of second layer of 14) over said first metal layer;

a first dielectric (white portion of layer 14) layer between said first and second metal layers;

a passivation layer (18, col 5 lines 4-5) over the metallization structure and over said dielectric layer, wherein a first opening in said passivation layer is over a first contact point (16) of said metallization structure and exposes said first contact point, and a second opening (16) in said passivation layer is over a second contact point of said metallization structure and exposes said second contact point, where said first and second contact points are separated from each other by an insulating material (the passivation layer 18) and wherein said passivation layer comprises silicon nitride (col 5 lines 4-5); and

a circuit trace (26/22/36/28/38) over the passivation layer and over said first and second contact points (16), wherein said first contact point is connected to said second contact point through said circuit trace (38/28/38 connect first and second points 16), and wherein said circuit trace is connected to said resistor (col 4 lines 66-67, col 5 line 1-2 describe point of contact 16 as connected to the transistors and other devices on the surface of substrate 10, which would include the resistor. col 5 lines describe contact point 16 also in electrical contact with 22/36/38, which is the circuit trace. Thus the resistor on surface of substrate is connected to the circuit trace through contact 16) through said first opening (16).

Lin fails to disclose the resistor in said silicon substrate comprises silicon with a dopant. Woolery teaches a chip structure (Figures 4A-4J) with a silicon substrate (400) and a resistor ("Resistor") in said silicon substrate, where said resistor comprises silicon with a dopant (arsenic, col 9 lines 53-56). It would have been obvious to one of ordinary skill in the art at the time the invention was made to modify Lin to have a resistor in the

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silicon substrate where said resistor comprises silicon with a dopant as in Woolrey in order to be able to predetermine and set the device resistivity.

Re claim 89: Lin discloses a chip structure comprising:

a silicon substrate (10, col 4 line 49);

a resistor in said silicon substrate (not shown but “transistors and other devices” is described in col 4 lines 49-51),

a MOS device (not shown but described as “transistors and other devices” in col 4 lines 49-51) comprising a portion in said silicon substrate;

a metallization structure (14) over said silicon substrate, wherein said metallization structure comprises a first metal layer (interconnect portion 13 of first layer of 14) and a second metal layer (interconnect portion 13 of second layer of 14) over said first metal layer;

a dielectric (white portion of layer 14) layer between said first and second metal layers;

a passivation layer (18, col 5 lines 4-5) over the metallization structure and over said dielectric layer; wherein a first opening in said passivation layer is over a first contact point (16) of said metallization structure and exposes said first contact point, and a second opening (16) in said passivation layer is over a second contact point of said metallization structure and exposes said second contact point, where said first and second contact points are separated from each other by an insulating material (the passivation layer 18) and

a circuit trace (26/22/36/28/38) over the passivation layer and over said first and second contact points (16), wherein said first contact point is connected to said second contact point through said circuit trace (38/28/38 connect first and second points 16),, wherein said circuit trace is connected to said resistor (col 4 lines 66-67, col 5 line 1-2 describe point of contact 16 as connected to the transistors and other devices on the surface of substrate 10, which would include the resistor. col 5 lines describe contact point 16 also in electrical contact with 22/36/38, which is the circuit trace. Thus the resistor on surface of substrate is connected to the circuit trace through contact 16) through said first opening (16)., and wherein said circuit trace comprises a third metal layer (copper, tungsten, nickel col 6 lines 55-57) and a copper layer (electroplating copper, col 6 lines 57) over said third metal layer.

Lin fails to disclose the resistor in said silicon substrate comprises silicon with a dopant. Woolery teaches a chip structure (Figures 4A-4J) with a silicon substrate (400) and a resistor ("Resistor") in said silicon substrate, where said resistor comprises silicon with a dopant (arsenic, col 9 lines 53-56). It would have been obvious to one of ordinary skill in the art at the time the invention was made to modify Lin to have a resistor in the silicon substrate where said resistor comprises silicon with a dopant as in Woolrey in order to be able to predetermine and set the device resistivity.

Re claims 48-53 and 94-99: Lin discloses a polymer layer (20) between the passivation/silicon-nitride layer (18) and the circuit trace (26/22/21/36/28) and on the circuit trace where the polymer layer comprises polyimide (PI) or benzocyclobutene (BCB), (col 5, lines 19 and 23-27).

Claims 54-56 and 59 are rejected under 35 U.S.C. 103(a) as being unpatentable over U.S. Pat. No. 6,495,442 to Lin et al (Lin) in view of U.S. Pat. No. 6,528,380 to Woolery et al. (Woolery) and U.S. Pat. No. 6,235,101 to Erdejac et al. (Erdejac).

Re claims 54-56: Lin discloses the circuit structure as claimed in 43. Lin fails to explicitly disclose the structure comprising an inductor over said passivation layer where said inductor comprises a copper layer. Erdejac teaches an inductor (top metal inductor Fig 20c) over said passivation layer where said inductor comprises a copper layer (col 6 lines 65-68) and gold layer (col 7 line 25-26). It would have been obvious to one of ordinary skill in the art at the time the invention was made to modify Lin to have the inductor as in Erdejac in order to create a circuit structure for specific applications such as RF.

Re claim 59: Lin discloses the circuit structure as claimed in 43. Lin fails to explicitly disclose the structure comprising a capacitor over said silicon substrate, where said capacitor comprises a first electrode over the substrate and a second electrode over the first electrode and a second dielectric layer between the first and second electrodes wherein a third opening in the passivation layer is over the first electrode and exposes said first electrode. Erdejac teaches a capacitor (Fig 20b, poly poly capacitor) over said silicon substrate, where said capacitor comprises a first electrode (poly 0) over the substrate and a second electrode (poly 1) over the first electrode and a second dielectric layer between the first and second electrodes wherein a third opening in the passivation layer is over the first electrode (opening for metal 1) and exposes said first

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electrode. It would have been obvious to one of ordinary skill in the art at the time the invention was made to modify Lin to include the capacitor as in Erdejac in order to create a circuit structure for specific applications such as RF.

Claims 64, 57, 60-63, 69-74, 83 and 100-101 are rejected under 35 U.S.C.

103(a) as being unpatentable over U.S. Pat. No. 6,495,442 to Lin et al (Lin) in view of U.S. Pat. No. 6,528,380 to Woolery et al. (Woolery) and U.S. Pat. No. 5,972,734 to Carichner et al. (Carichner) or U.S. Pat. No. 6,495,442 to Lin et al (Lin) in view of U.S. Pat. No. 6,528,380 to Woolery et al. (Woolery) and U.S. Pat. No. 6,235,101 to Erdejac et al. (Erdejac) and U.S. Pat. No. 5,972,734 to Carichner et al. (Carichner).

Re claim 64: Lin discloses a chip structure comprising:

a silicon substrate (10, col 4 line 49);

a resistor in said silicon substrate (not shown but “transistors and other devices” is described in col 4 lines 49-51),

a MOS device (not shown but described as “transistors and other devices” in col 4 lines 49-51) comprising a portion in said silicon substrate;

a metallization structure (14) over said silicon substrate, wherein said metallization structure comprises a first metal layer (interconnect portion 13 of first layer of 14) and a second metal layer (interconnect portion 13 of second layer of 14) over said first metal layer;

a dielectric (white portion of layer 14) layer between said first and second metal layers;

a passivation layer (18, col 5 lines 4-5) over the metallization structure and over said dielectric layer, herein a first opening in said passivation layer is over a first contact point (16) of said metallization structure and exposes said first contact point, and a second opening (16) in said passivation layer is over a second contact point of said metallization structure and exposes said second contact point, where said first and second contact points are separated from each other by an insulating material (the passivation layer 18) and wherein said passivation layer comprises silicon nitride; and

a circuit trace (26/22/36/28/38) over the passivation layer and over said first and second contact points (16), wherein said first contact point is connected to said second contact point through said circuit trace (38/28/38 connect first and second points 16), wherein said circuit trace is connected to said resistor (col 4 lines 66-67, col 5 line 1-2 describe point of contact 16 as connected to the transistors and other devices on the surface of substrate 10, which would include the resistor. col 5 lines describe contact point 16 also in electrical contact with 22/36/38, which is the circuit trace. Thus the resistor on surface of substrate is connected to the circuit trace through contact 16) through said first opening (16).

Lin fails to disclose the resistor in said silicon substrate comprises silicon with a dopant. Woolery teaches a chip structure (Figures 4A-4J) with a silicon substrate (400) and a resistor ("Resistor") in said silicon substrate, where said resistor comprises silicon with a dopant (arsenic, col 9 lines 53-56). It would have been obvious to one of ordinary

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skill in the art at the time the invention was made to modify Lin to have a resistor in the silicon substrate where said resistor comprises silicon with a dopant as in Woolrey in order to be able to predetermine and set the device resistivity.

Lin also fails to disclose where said circuit trace comprises a titanium-containing layer and a gold layer over said titanium-containing layer. Carichner teaches a circuit trace (212) comprises a titanium-containing layer and a gold layer over said titanium-containing layer (col 4 lines 41-46). It would have been obvious to one of ordinary skill in the art at the time the invention was made to modify Lin to include the different circuit trace and metallization layers of Charichner in order to optimize the device performance under thermal stress.

Re claims 57, 60-63, 83 and 100-101: Lin as modified discloses the device of 43, 65 and 89 as above where the circuit trace comprises a nickel layer over a copper layer. Lin fails to disclose the circuit trace comprising a gold layer over the copper layer, a titanium layer under the copper layer, a titanium-containing layer comprising tungsten, a chromium layer under the copper layer, a gold layer, a titanium-containing layer under gold layer and a titanium-containing layer comprising tungsten. Carichner teaches a circuit trace (212) comprises a nickel layer over a copper layer. Lin fails to disclose the circuit trace comprising a gold layer over the copper layer, a titanium layer under the copper layer, a titanium-containing layer comprising tungsten, a chromium layer under the copper layer, a gold layer, a titanium-containing layer under gold layer and a titanium-containing layer comprising tungsten (col 4 lines 41-46). It would have been obvious to one of ordinary skill in the art at the time the invention was made to modify Lin to

include the different circuit trace and metallization layers of Charichner in order to optimize the device performance under thermal stress.

Re claims 69-74: Lin discloses a polymer layer (20) between the passivation/silicon-nitride layer (18) and the circuit trace (26/22/21/36/28) and on the circuit trace where the polymer layer comprises polyimide (PI) or benzocyclobutene (BCB), (col 5, lines 19 and 23-27).

Claims 84 and 102 are rejected under 35 U.S.C. 103(a) as being unpatentable over U.S. Pat. No. 6,495,442 to Lin et al (Lin) in view of U.S. Pat. No. 6,528,380 to Woolery et al. (Woolery) as applied to claims 48 and 89 above and U.S. Pat. No. 6,495,442 to Lin et al (Lin) in view of U.S. Pat. No. 6,528,380 to Woolery et al. (Woolery) and U.S. Pat. No. 5,972,734 to Carichner et al. (Carichner) as applied to claim 64 above in further view of and U.S. Pub. No. 2002/0047210 to Yamada et al. (Yamada).

Re claims 84 and 102: Lin as modified fails to disclose where the metallization structure comprises aluminum. Yamada discloses metallization structures comprising aluminum (for example in paragraphs [0163] and [0176]). It would have been obvious to one of ordinary skill in the art at the time the invention was made to adapt Lin to include aluminum in the metallization in order to provide desirable conductivity.

Claims 44-46, 65-67, 90-92 are rejected under 35 U.S.C. 103(a) as being unpatentable over U.S. Pat. No. 6,495,442 to Lin et al (Lin) in view of U.S. Pat. No. 6,528,380 to Woolery et al. (Woolery) as applied to claims 44 and 89 above and U.S. Pat. No. 6,495,442 to Lin et al (Lin) in view of U.S. Pat. No. 6,528,380 to Woolery et al. (Woolery) and U.S. Pat. No. 5,972,734 to Carichner et al. (Carichner) as applied to claim 64 above and in further view of U.S. Pub. No. 2003/0155570 to Leidy.

Re claims 44-46, 65-67, 90-92, Lin as modified discloses the device of 43, 65, and 89 as above. The modification of Woolery also discloses the resistor comprising silicon with a dopant of arsenic (col 9 lines 51 line 6). Lin as modified fails to disclose the resistor comprising silicon with a dopant of boron, phosphorous. Leidy teaches a resistor comprising silicon and a dopant of boron, phosphorous, or arsenic (page 5, claim 26). It would have been obvious to one of ordinary skill in the art at the time the invention was made to modify Lin to have the resistor made of silicon and a dopant of boron, phosphorous, or arsenic as in Leidy in order to be able to predetermine the device resistivity (Leidy, page 3, paragraph 37).

Claims 45, 47, 66, 68, 91 and 93 are rejected under 35 U.S.C. 103(a) as being unpatentable over U.S. Pat. No. 6,495,442 to Lin et al (Lin) in view of U.S. Pat. No. 6,528,380 to Woolery et al. (Woolery) as applied to claims 48 and 89 above and U.S. Pat. No. 6,495,442 to Lin et al (Lin) in view of U.S. Pat. No. 6,528,380 to Woolery et al. (Woolery) and U.S. Pat. No. 5,972,734 to Carichner et al. (Carichner) as applied to claim 64 above in further view of and U.S. Pub. No. 2003/0183332 to Simila.

Re claims 45, 47, 66, 68, 91 and 93: Lin discloses the device of 43 and 65 as above. The modification of Woolery also discloses the resistor comprising silicon with a dopant of arsenic (col 9 lines 51 line 6). Lin as modified fails to disclose the resistor comprising silicon with a dopant of phosphorous or gallium. Simila a resistor comprising silicon and a dopant of phosphorous or gallium (paragraph 70). It would have been obvious to one of ordinary skill in the art at the time the invention was made to modify Lin to have the resistor made of silicon and a dopant of phosphorous or gallium as in Simila in order to be able to predetermine the device resistivity.

Response to Arguments

Applicant's arguments filed 05/13/2008 have been fully considered but they are not persuasive.

Applicant argues that Lin fails to disclose a resistor in the silicon substrate. Examiner disagrees. Lin discloses there are "transistors and other devices" in the silicon substrate and one of ordinary skill in the art at the time the invention was made would interpret this disclosure to include resistors.

Conclusion

Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Colleen A. Matthews whose telephone number is (571)272-1667. The examiner can normally be reached on Monday - Friday 8AM-4:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Lynne Gurley can be reached on 571-272-1670. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

/C. A. M./
Examiner, Art Unit 2811

/Lynne A. Gurley/
Supervisory Patent Examiner, Art
Unit 2811